

MBR620FCT - MBR6100FCT

6.0A DUAL SCHOTTKY BARRIER RECTIFIER

Features

- Power Schottky Barrier Chip
- Guard Ring for Transient Protection
- Low Forward Voltage Drop
- Low Power Loss, High Efficiency
- High Surge Current Capability
- Epoxy Meets UL 94V-0 Classification
- Ideally Suited for Use in High Frequency SMPS, Inverters and As Free Wheeling Diodes

Mechanical Data

Case: ITO-220, Full Molded PlasticTerminals: Plated Leads Solderable per

MIL-STD-202, Method 208 Polarity: See Diagram

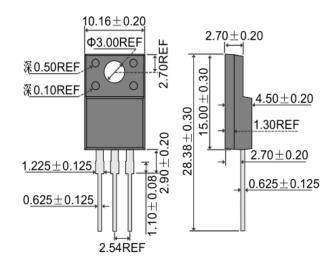
Weight: 1.9 grams (approx.)

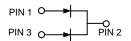
Mounting Position: Any

Mounting Torque: 0.6 N.m Max.

Lead Free: For RoHS / Lead Free Version

ITO-220AB





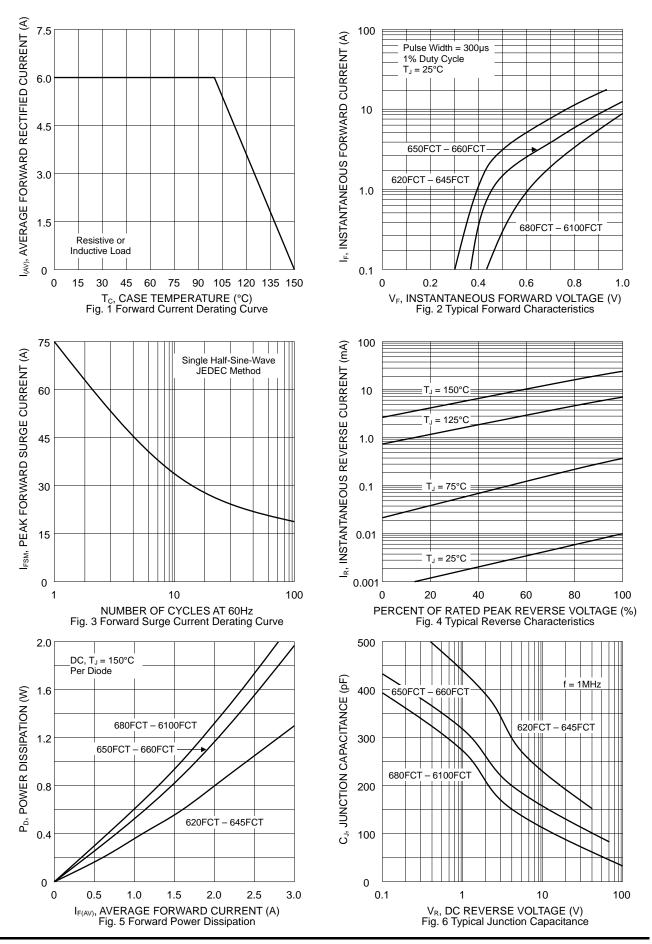
Maximum Ratings and Electrical Characteristics @TA=25°C unless otherwise specified

Single Phase, half wave, 60Hz, resistive or inductive load. For capacitive load, derate current by 20%.

| Characteristic | Symbol | MBR 620FCT | MBR 630FCT | MBR 640FCT | MBR 645FCT | MBR 650FCT | MBR 660FCT | MBR 680FCT | MBR 6100FCT | Unit |
|---|--------------------|---------------|---------------|---------------|---------------|---------------|---------------|---------------|----------------|------|
| Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage | VRRM VRWM VR | 20 | 30 | 40 | 45 | 50 | 60 | 80 | 100 | ٧ |
| RMS Reverse Voltage | VR(RMS) | 14 | 21 | 28 | 32 | 35 | 42 | 56 | 70 | V |
| Average Rectified Output Current $@T_C = 100$ °C Total Device Per Diode | lo | 6.0 3.0 | | | | | | | | Α |
| Non-Repetitive Peak Forward Surge Current 8.3ms Single Half Sine-Wave Superimposed on Rated Load (JEDEC Method) | IFSM | 75 | | | | | | Α | | |
| Forward Voltage per diode @I _F = 3.0A | VFM | 0.55 0.75 | | | 75 | 0. | 85 | V | | |
| Peak Reverse Current $@T_J = 25^{\circ}C$ At Rated DC Blocking Voltage $@T_J = 100^{\circ}C$ | IRM | 0.2 15 | | | | | | | mA | |
| Typical Junction Capacitance (Note 1) | Cı | 300 | | | 20 | 200 15 | | 50 | pF | |
| Thermal Resistance Junction to Ambient per diode Thermal Resistance Junction to Case per diode | R JA R JC | 62 4.5 | | | | | | | °C/W | |
| RMS Isolation Voltage, t = 1 min | Viso | 1500 | | | | | | V | | |
| Operating and Storage Temperature Range | ТJ, Tsтg | -55 to +150 | | | | | | °C | | |

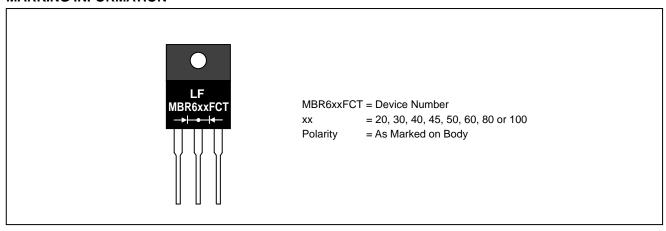
Note: 1. Measured at 1.0 MHz and applied reverse voltage of 4.0V D.C.

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MARKING INFORMATION



PACKAGING INFORMATION

BULK

| Tube Size | Quantity | Inner Box Size | Quantity | Carton Size | Quantity | Approx. Gross Weight (KG) |
|----------------|----------|----------------|----------|-----------------|----------|---------------------------|
| L x W x H (mm) | (PCS) | L x W x H (mm) | (PCS) | L x W x H (mm) | (PCS) | |
| 525 x 31 x 6 | 50 | 558 x 150 x 40 | 1,000 | 570 x 235 x 170 | 5,000 | 11.85 |

RECOMMENDED SCREW MOUNTING ARRANGEMENT

The full molded plastic package affords a major reduction of hardware as compared to a standard TO-220 package. However, precautions should be made in mounting procedure.

A conical washer should be used to apply proper force to the device. Screw should not be tightened with any type of air-forced torque or equipment that may cause crack on device package.

A layer of thermal grease or thermal pad in the interface will be considerably helpful for heat dissipation.

